

Amendments to the specification

Please make the following amendments to the specification:

On page 4, lines 23-25, please make the following amendment

[0030] According to still a further feature of the method of the invention, the first and second pattern layers are layers of polycrystalline silicon or metal, or nitride, or silicon, or silica, or [[HiK]] High-K material.

On page 6, lines 22-26, please make the following amendment

The first pattern layer 5 has chemical etching selectivity relatively to silicon oxide. As this will appear subsequently, layer 5 is a layer in which the first pattern is formed. Generally, the first pattern layer 5 may for example be a layer of polycrystalline silicon, of metal, of silicon nitride (Si_3N_4), a High-K (also known as High-K dielectric) material or of gate insulator topped with a stack of gate layers.